

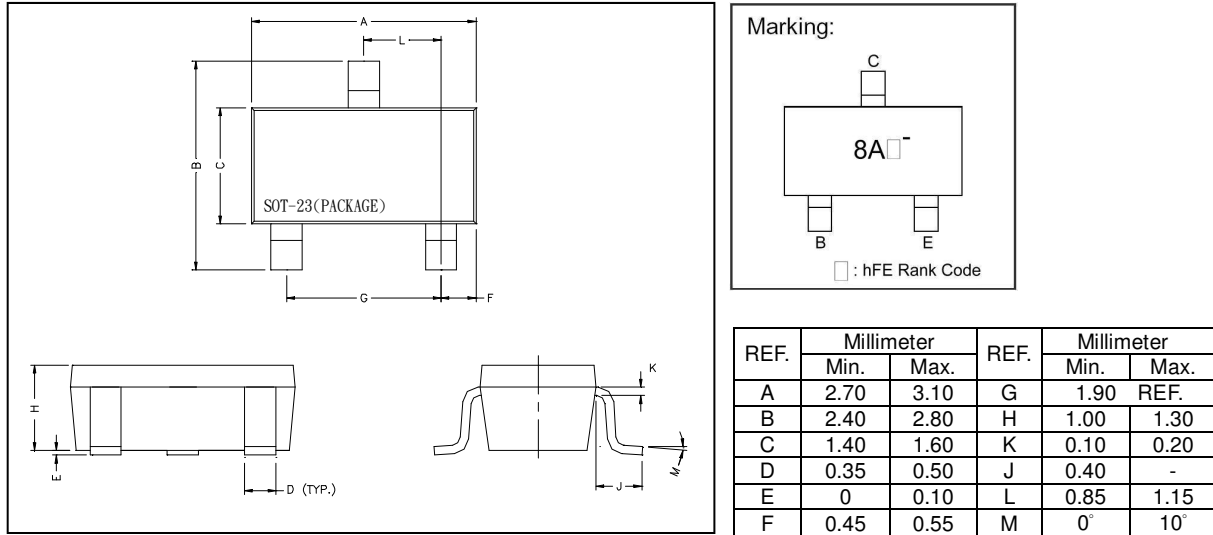
GBC846

NPN EPITAXIAL PLANAR TRANSISTOR

Description

The GBC846 is designed for switching and AF amplifier application, suitable for automatic insertion in thick and thin-film circuits.

Package Dimensions



Absolute Maximum Ratings at Ta = 25°C

Parameter	Symbol	Ratings	Unit
Junction Temperature	Tj	+150	°C
Storage Temperature	Tstg	-55 ~ +150	°C
Collector to Base Voltage	VCBO	80	V
Collector to Emitter Voltage	VCEO	65	V
Emitter to Base Voltage	VEBO	6	V
Collector Current	IC	100	mA
Total Power Dissipation	PD	250	mW

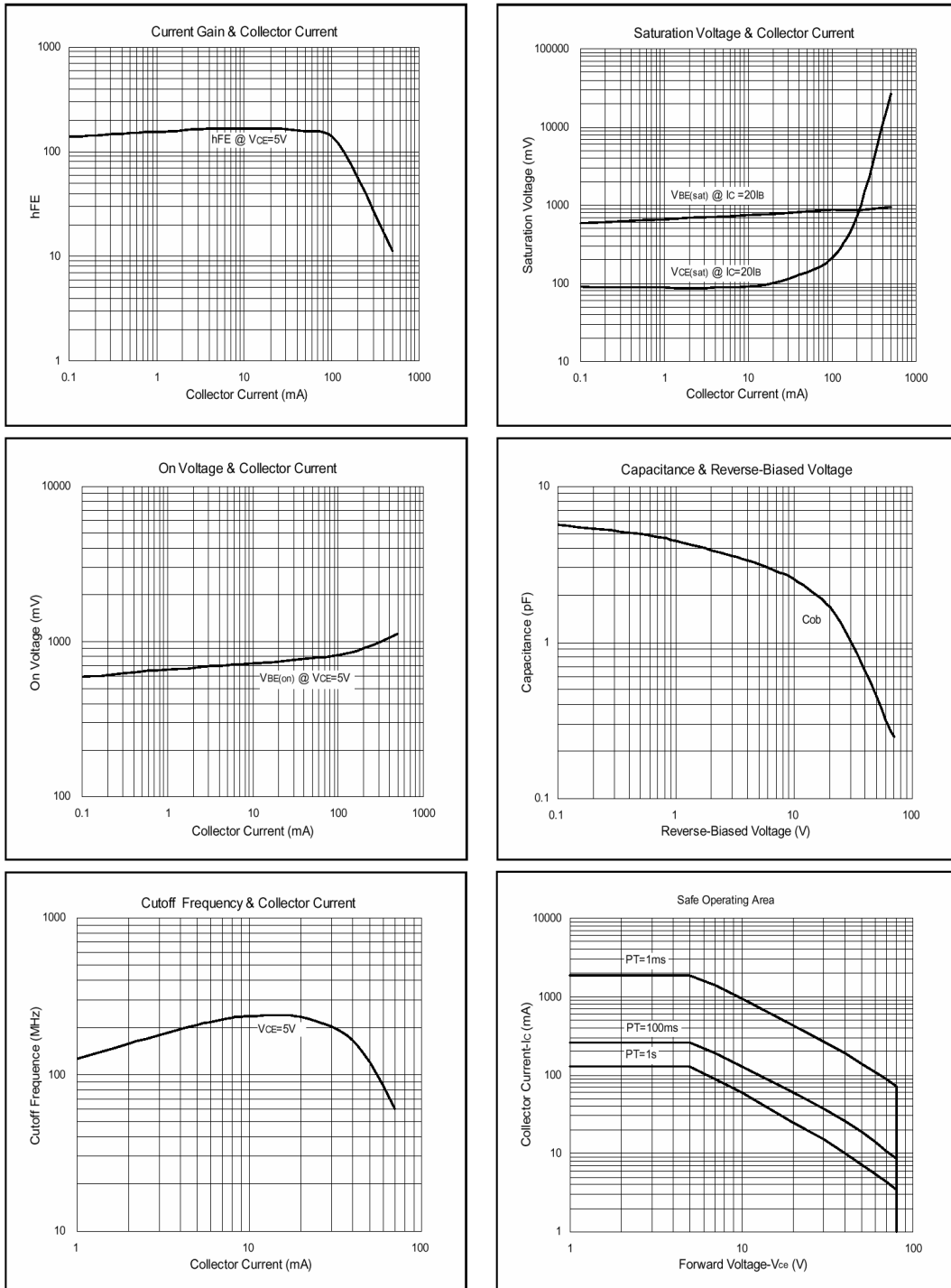
Characteristics at Ta = 25°C

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
BVCBO	80	-	-	V	IC=100uA
BVCEO	65	-	-	V	IC=1mA
BVEBO	6	-	-	V	IE=10uA
ICBO	-	-	15	nA	VCB=30V
VCE(sat)1	-	90	250	mV	IC=10mA, IB=0.5mA
VCE(sat)2	-	200	600	mV	IC=100mA, IB=5mA
VBE(sat)1	-	700	-	mV	IC=10mA, IB=0.5mA
VBE(sat)2	-	900	-	mV	IC=100mA, IB=5mA
VBE(on)1	580	-	700	mV	VCE=5V, IC=2mA
VBE(on)2	-	-	770	mV	VCE=5V, IC=10mA
hFE	110	-	800		VCE=5V, IC=2mA
fT	-	300	-	MHz	VCE=5V, IC=10mA
Cob	-	3.5	6	pF	VCB=10V, f=1MHz, IE=0A

Classification Of hFE

Rank	A	B	C
hFE	110-220	200-450	420-800

Characteristics Curve



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